David M Hoffman

List of Publications by Year
in descending order

45 papers	2,166 citations	236925 25 h-index	254184 43 g-index
45 all docs	45 docs citations	45 times ranked	1384 citing authors

#	Article	IF	Citations
1	Synthesis of Copper(I) Complexes with Ketimide and Hydrazide Ligands. Journal of Cluster Science, 2010, 21, 567-575.	3.3	20
2	Synthesis of (Hydrazonido)aluminum Complexes. European Journal of Inorganic Chemistry, 2008, 2008, 5251-5256.	2.0	4
3	Synthesis and structures of Group 4 trimethylhydrazido complexes. Inorganica Chimica Acta, 2003, 345, 327-332.	2.4	12
4	Synthesis and Structures of Zirconium Amideâ^'Iodide Complexes. Inorganic Chemistry, 2002, 41, 4063-4067.	4.0	9
5	Synthesis of Homoleptic Gallium Alkoxide Complexes and the Chemical Vapor Deposition of Gallium Oxide Films. Chemistry of Materials, 2001, 13, 2135-2143.	6.7	88
6	General Synthesis of Homoleptic Indium Alkoxide Complexes and the Chemical Vapor Deposition of Indium Oxide Films. Journal of the American Chemical Society, 2000, 122, 9396-9404.	13.7	56
7	Low pressure chemical vapor deposition of fluorine-doped indium oxide films from an indium alkoxide complex. Journal of Materials Chemistry, 2000, 10, 2392-2395.	6.7	22
8	Low temperature chemical vapor deposition of titanium nitride films from tetrakis(ethylmethylamido)titanium and ammonia. Thin Solid Films, 1999, 357, 125-131.	1.8	25
9	Atmospheric-pressure chemical vapor deposition of fluorine-doped tin oxide thin films. Thin Solid Films, 1999, 345, 240-243.	1.8	40
10	Synthesis of aluminium and gallium fluoroalkoxide compounds and the low pressure metal-organic chemical vapor deposition of gallium oxide films. Journal of Materials Chemistry, 1999, 9, 929-935.	6.7	53
11	Indium Fluoroalkoxide Compounds. Inorganic Chemistry, 1999, 38, 4447-4454.	4.0	37
12	Synthesis of Indium Amide Compounds. Inorganic Chemistry, 1998, 37, 3835-3841.	4.0	34
13	Indium Tris(alkylthiolate) Compounds. Inorganic Chemistry, 1998, 37, 5823-5826.	4.0	23
14	Further studies of the reactions involving ethyne and M2(OBut)6, where M î—» Mo and W. Polyacetylene formation versus formation of ethyne adducts and Cî—¸C coupled products. Polyhedron, 1997, 16, 839-847.	2.2	13
15	Synthesis of Tin Oxide Precursors and Related Germanium and Lead Compounds. Inorganic Chemistry, 1996, 35, 6164-6169.	4.0	47
16	Synthesis of Ferroelectric Strontium Bismuth Tantalate Films from Metal Alkoxide Precursors. Materials Research Society Symposia Proceedings, 1996, 453, 513.	0.1	0
17	Low-temperature atmospheric-pressure metal-organic chemical vapor deposition of molybdenum nitride thin films. Thin Solid Films, 1996, 288, 116-119.	1.8	35
18	Synthesis and Structural Characterization of Tantalum(IV) Amido Compounds. Inorganic Chemistry, 1996, 35, 5015-5018.	4.0	22

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19	Plasma Enhanced Chemical Vapor Deposition of Zirconium Nitride Thin Films. Materials Research Society Symposia Proceedings, 1995, 410, 289.	0.1	1
20	Plasma enhanced chemical vapor deposition of silicon nitride films from a metal-organic precursor. Journal of Materials Research, 1994, 9, 3019-3021.	2.6	9
21	Chemical vapour deposition of nitride thin films. Polyhedron, 1994, 13, 1169-1179.	2.2	148
22	Low Temperature Atmospheric Pressure Chemical Vapor Deposition of Group 14 Oxide Films. Materials Research Society Symposia Proceedings, 1994, 343, 523.	0.1	0
23	[Ni(PtBu)6] and[Ni(SiH2)6] Are Isolobal, Related to[In{Mn(CO)4}5]2â^', and Have 16-Electron Counts. Angewandte Chemie International Edition in English, 1993, 32, 1616-1618.	4.4	22
24	Syntheses and x-ray crystal structures of tetrakis(diphenylamido)niobium(IV) and niobium(IV) amido-halide complexes. Polyhedron, 1993, 12, 2899-2900.	2.2	9
25	Chemical vapor deposition of vanadium, niobium, and tantalum nitride thin films. Chemistry of Materials, 1993, 5, 614-619.	6.7	165
26	[Ni(PtBu)₆] und [Ni(SiH₂)₆] sind isolobal, verwandt mit [In{Mn(CO)₄}₅]^{2â^'} und haben jeweils 16 Valenzelektronen. Angewandte Chemie, 1993, 105, 1682-1684.	2.0	5
27	Plasma Enhanced Metal-Organic Chemical Vapor Deposition of Germanium Nitride Thin Films. Materials Research Society Symposia Proceedings, 1993, 335, 3.	0.1	1
28	Low Temperature Preparation of Gallium Nitride Thin Films. Materials Research Society Symposia Proceedings, 1992, 242, 445.	0.1	7
29	Chemical vapor deposition of aluminum nitride thin films. Journal of Materials Research, 1992, 7, 1679-1684.	2.6	41
30	Low-temperature atmospheric pressure chemical vapor deposition of polycrystalline tin nitride thin films. Chemistry of Materials, 1992, 4, 68-71.	6.7	53
31	Chemical vapor deposition of titanium, zirconium, and hafnium nitride thin films. Chemistry of Materials, 1991, 3, 1138-1148.	6.7	210
32	Atmospheric pressure chemical vapor deposition of aluminum nitride thin films at 200â€“250 Â°C. Journal of Materials Research, 1991, 6, 5-7.	2.6	41
33	Atmospheric Pressure Chemical Vapor Deposition of Gallium Nitride Thin Films. Materials Research Society Symposia Proceedings, 1990, 204, 95.	0.1	11
34	Silicon dimethylamido complexes and ammonia as precursors for the atmospheric pressure chemical vapor deposition of silicon nitride thin films. Chemistry of Materials, 1990, 2, 480-482.	6.7	33
35	Synthesis of thin films by atmospheric pressure chemical vapor deposition using amido and imido titanium(IV) compounds as precursors. Chemistry of Materials, 1990, 2, 235-241.	6.7	192
36	Solution-phase reactivity as a guide to the low-temperature chemical vapor deposition of early-transition-metal nitride thin films. Journal of the American Chemical Society, 1990, 112, 7833-7835.	13.7	83

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37	Organometallchemie mit MolybdÃnâ€•und Wolframalkoxidclustern; Vergleich mit Carbonylclustern der spÄten Ãœbergangsmetalle. Angewandte Chemie, 1989, 101, 446-458.	2.0	12
38	Titanium Nitride Thin Films: Properties and Apcvd Synthesis Using Organometallic Precursors. Materials Research Society Symposia Proceedings, 1989, 168, 357.	0.1	31
39	Synthese und Struktur eines resonanzstabilisierten (Trimethylphosphonio)metallapropenids. Angewandte Chemie, 1988, 100, 585-587.	2.0	6
40	Reactions involving alkynes and tungsten-tungsten triple bonds supported by alkoxide ligands. Polyhedron, 1987, 6, 783-792.	2.2	35
41	Metal alkoxides: models for metal oxides. 7. Trinuclear and tetranuclear alkylidyne clusters of tungsten supported by alkoxide ligands. Journal of the American Chemical Society, 1985, 107, 1234-1241.	13.7	36
42	Metal alkoxides: models for metal oxides. 4. Alkyne adducts of ditungsten hexaalkoxides and evidence for an equilibrium between dimetallatetrahedrane and methylidynemetal complexes: W2(.mu.-C2H2) .dblharw. 2W.tplbond.CH. Journal of the American Chemical Society, 1984, 106, 6794-6805.	13.7	95
43	Metal alkoxides models for metal oxides. 5. Coupling of alkyne ligands in reactions involving ditungsten hexaalkoxides: an alternative to the metathesis reaction M.tplbond.M + C.tplbond.C- .fwdarw. 2M.tplbond.C. Journal of the American Chemical Society, 1984, 106, 6806-6815.	13.7	53
44	Isoelectronic molecules with triple bonds to metal atoms (M = Mo, W): crystal and molecular structures of tri-tert-butoxytungsten ethylidyne and nitride. Inorganic Chemistry, 1983, 22, 2903-2906.	4.0	100
45	Perpendicular and parallel acetylene complexes. Journal of the American Chemical Society, 1982, 104, 3858-3875.	13.7	227